

# Midium Power Transistors (30V / 1A) 2SCR293P

#### Structure

NPN Silicon epitaxial planar transistor

# Features

Low saturation voltage  $V_{CE (sat)}$  = 0.35V (Max.) (I<sub>C</sub> / I<sub>B</sub>= 500mA / 25mA)

# Applications

Driver

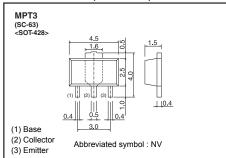
#### Packaging specifications

	Package	MPT3
Туре	Code	T100
	Basic ordering unit (pieces)	1000

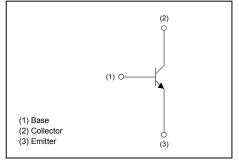
# •Absolute maximum ratings (Ta=25°C)

Para	imeter	Symbol	Limits	Unit
Collector-base voltage		V <sub>CBO</sub>	30	V
Collector-emitter voltage		V <sub>CEO</sub>	30	V
Emitter-base voltage	ge	$V_{EBO}$	6	V
Collector current	DC	Ι <sub>c</sub>	1	А
	Pulsed	I <sub>CP</sub> *1	2	А
Power dissipation	$P_D * 2  0.5  W$		W	
		P <sub>D</sub> *3	2.0	W
Junction temperature		Tj	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to 150	°C

# • Dimensions (Unit : mm)



#### • Inner circuit (Unit : mm)



\*1 Pw=10ms, Single Pulse

\*2 Mounted on a recommended land

\*3 Mounted on a 40×40×0.7 [mm] ceramic substrate

# •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	$BV_{CEO}$	30	-	-	V	I <sub>C</sub> = 1mA
Collector-base breakdown voltage	$BV_{CBO}$	30	-	-	V	Ι <sub>C</sub> = 10μΑ
Emitter-base breakdown voltage	$BV_{EBO}$	6	-	-	V	Ι <sub>Ε</sub> = 10μΑ
Collector cut-off current	I <sub>CBO</sub>	-	-	100	nA	V <sub>CB</sub> = 30V
Emitter cut-off current	I <sub>EBO</sub>	-	-	100	nA	V <sub>EB</sub> = 6V
Collector-emitter staturation voltage	V <sub>CE(sat)</sub> <sup>*</sup> 1	-	120	350	mV	I <sub>C</sub> = 500mA, I <sub>B</sub> = 25mA
DC current gain	$h_{\text{FE}}$	270	-	680	-	V <sub>CE</sub> = 2V, I <sub>C</sub> = 100mA
Transition frequency	$f_{T}^{*1}$	-	320	-	MHz	V <sub>CE</sub> = 2V I <sub>E</sub> =-100mA, f=100MHz
Collector output capacitance	C <sub>ob</sub>	-	7	-	pF	V <sub>CB</sub> = 10V, I <sub>E</sub> =0A f=1MHz
Turn-on time	t <sub>on</sub> * <sub>2</sub>	-	90	-	ns	1 - 500mA = -25mA
Storage time	t <sub>stg</sub> * <sub>2</sub>	-	300	-	ns	I <sub>C</sub> = 500mA, I <sub>B1</sub> = 25mA, I <sub>B2</sub> = -25mA, V <sub>CC</sub> <u>~</u> 5V
Fall time	t <sub>f</sub> *2	-	60	_	ns	·B2 _0···· ·; • (() _0 •

\*1 Pulsed

\*2 See switching time test circuit

# •Electrical characteristic curves (Ta=25°C)

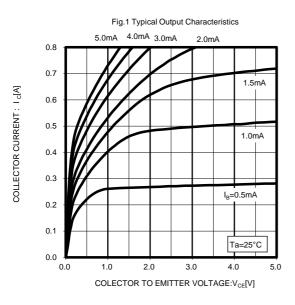


Fig.3 DC Current Gain vs. Collector Current( II )

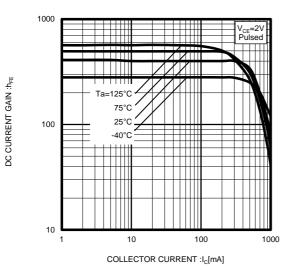


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current( II )

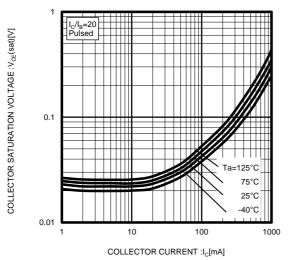


Fig.2 DC Current Gain vs. Collector Current( I )

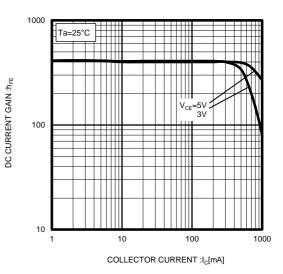
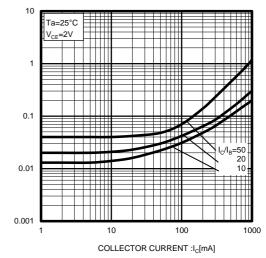
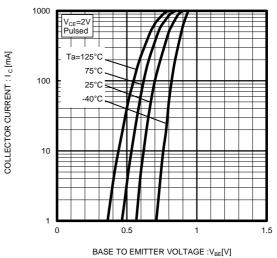


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current( I )









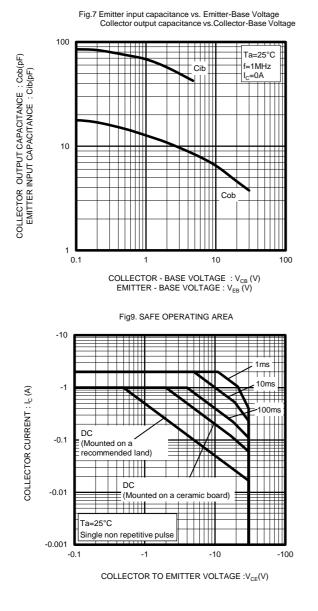
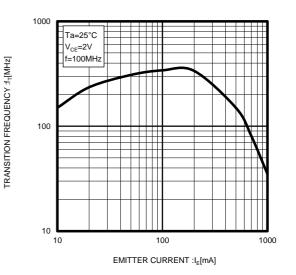
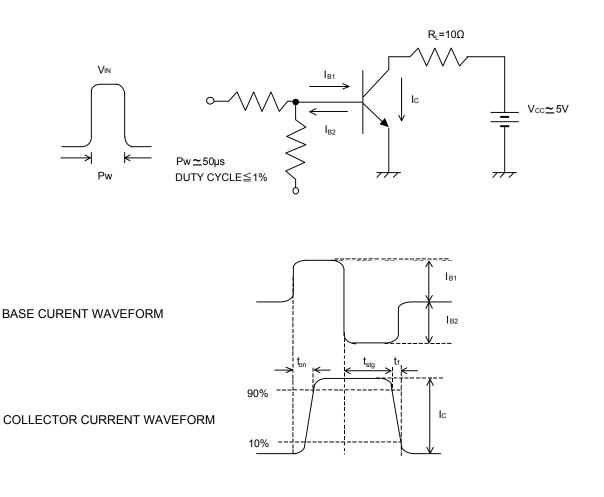


Fig8. Gain Bandwidth Product vs. Emitter Current



# • Switching time test circuit



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